

ABSTRACT:

The invention relates to the manufacture of a so-called LDMOSFET, in which a gate oxide (1) layer is not only deposited under the gate electrode (1) but also on both sides thereof. Against the sides of the gate electrode (1), which comprises silicon nitride, spacers (5) are positioned, which comprise a material that is selectively removable from the material of the gate oxide layer (1). The drain (3) is provided with a lightly doped part (3A) bordering the gate electrode (1).

According to the invention the lightly doped part (3A) of the drain (3) is formed by means of two additional masking layers (6,7) and the drain (3) is positioned at a distance from the gate electrode (1) which is larger than the width of the spacers (5). Preferably, the spacers (5) are used for silicidation of the gate electrode (1). In this way the method results in a particularly simple manner in a discrete LDSMOST that is highly suitable for application in a base station of a mobile telephone system wherein a high operating voltage and a high frequency are requested. Preferably, a shielding electrode (27) is positioned over the gate electrode (1).

Figure 1